

IGBT Transistor Module

MG100J6ES50

600V / 100A

DATASHEET

OEM – Toshiba

Source: Toshiba Databook 1995/96

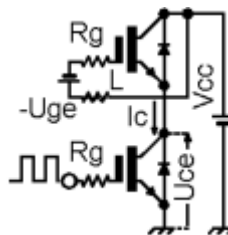
MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Emitter Voltage		Vces	600	V
Gate-Emitter Voltage		Vges	+/-20	V
Collector Current	DC	IC	100	A
	1ms	Icp	200	A
Forward Current	DC	If	100	A
	1ms	Ifm	200	A
Collector Power Dissipation		Pc	450	W
Junction Temperature		Tj	150	°C
Storage Temperature Range		Tstg	-40~125	°C
Isolation Voltage		Visol	2500 (AC 1min.)	V
Screw Torque		-	3/3	N*m

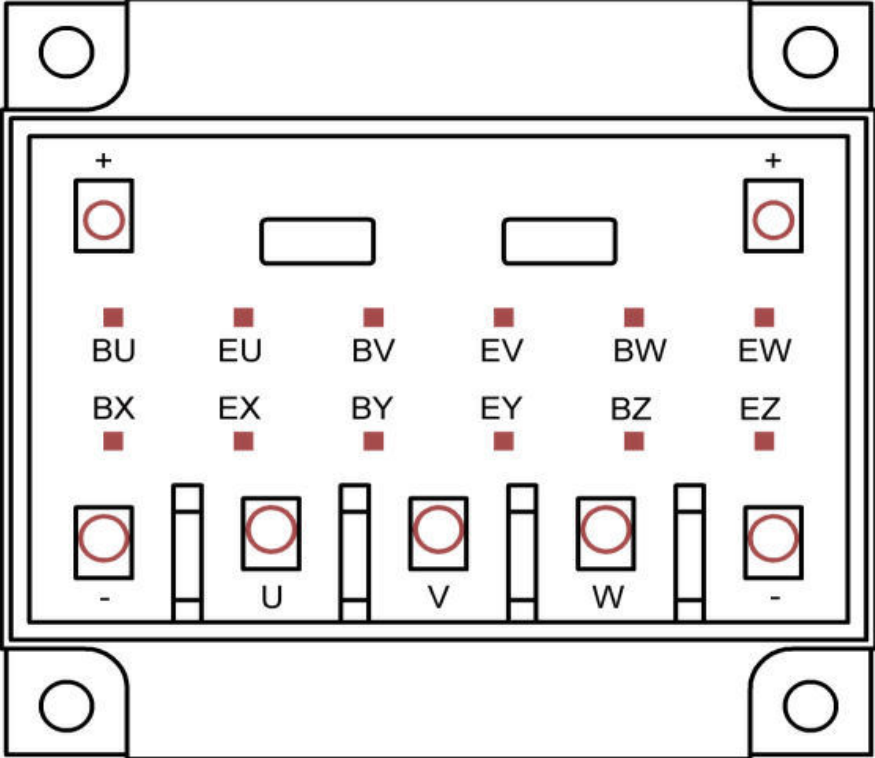
ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTICS		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		Iges	Uge=+/-20V, Vce=0	-	-	+500	nA
Collector Cut-off Current		Ices	Uce=600V, Uge=0	-	-	1.0	mA
Gate-Emitter Cut-off Voltage		Uge (off)	Ic=10mA, Uce=5V	5.0	7.0	8.0	V
Collector-Emitter Saturation Voltage		Uce (sat)	IC=100A, Uge=15V	-	2.1	2.7	V
Input Capacitance		Cies	Uce=10V, Uge=0, f=1MHz	-	9000	-	pF
Switching Time	Turn-on Delay	td(on)	Inductive Load Vcc=300V, Ic=100A, Uge=+/-15V, Rg=13R (Note1)	-	0.08	0.16	uS
	Rise Time	tr		-	0.12	0.24	
	Turn-on Time	ton		-	0.40	0.80	
	Turn-off Delay	td (off)		-	0.20	0.40	
	Fall Time	tf		-	0.15	0.30	
	Turn-off Time	toff		-	0.50	1.00	
Forward Voltage		Vf	If=100A, Uge=0	-	2.30	3.00	V
Reverse Recovery Time		trr	If=100A, Uge=-10V di/dt=100A/uS	-	0.08	0.15	uS
Thermal Resistance	Rth (j-c)	Transistor		-	-	0.28	°C/W
		Diode		-	-	0.69	

Note 1



2-94A2A



EQUIVALENT CIRCUIT

